Version With Markings To Show Changes Made

In the Specification:

Please insert the following text on page 1, line 1:

- Cross-Reference to Related Applications

The present application claims priority to Japanese Patent Application No. 2000-139537 filed May 12, 2000, the disclosure of which is incorporated herein by reference in its entirety. -

In the Claims:

Please delete Claims 5-8 for the purposes of rewriting.

Please insert the following new claims, Claims 9-16.

9. A resist material according to claim 1 wherein said or more surfactants having a fluorine substituent is selected from the group consisting of perfluoroalkylpolyoxyethylene ethanol, fluorinated alkyl ester, perfluoroalkylamine oxide, perfluoroalkylethylene oxide adduct, and fluorine-containing organosiloxane compounds.

10. A resist material according to claim 1 wherein said one or more surfactants having a fluorine substituent is present in an amount ranging from 10 to 2,000 ppm.

11. A resist material according to claim 1 wherein the weight ratio of the non-ionic surfactant having neither a fluorine substituent nor a silicon containing substituent to the surfactant containing a fluorine substituent is 0.1 or greater.

12. A resist material according to claim 11 wherein the weight ratio of the non-ionic surfactant having neither a fluorine substituent nor a silicon

containing substituent to the surfactant containing a fluorine substituent ranges from 0.1 to 100.

13. A method for forming a pattern on a substrate comprising:

coating a resist material on a substrate, the resist material comprising one or more surfactants having a fluorine substituent and one or more non-ionic surfactants having neither a fluorine substituent nor a silicon-containing substituent;

subjecting the substrate to heat to treat the substrate;

exposing the substrate through a photomask to radiation selected from the group consisting of high energy radiation having a wavelength of 500 nm or less, X-ray radiation, and electron beam radiation;

optionally heat treating the substrate; and

developing the substrate in a developing solution.

14. A method according to claim 13 wherein said non-ionic surfactant is one or more compounds selected from the group consisting of polyoxyalkylene alkyl ether esters, polyoxyalkylene alkyl ether, polyoxyalkylene dialkyl ether, polyoxyalkylene aralkyl alkyl ether, polyoxyalkylene aralkyl ether, polyoxyalkylene diaralkyl ether, and polyoxyalkylene laurylates.

15. A method according to claim 13 wherein the resist material is a chemically amplified resist material.

16. A method according to Claim 14 wherein the resist material is a chemically amplified resist material.